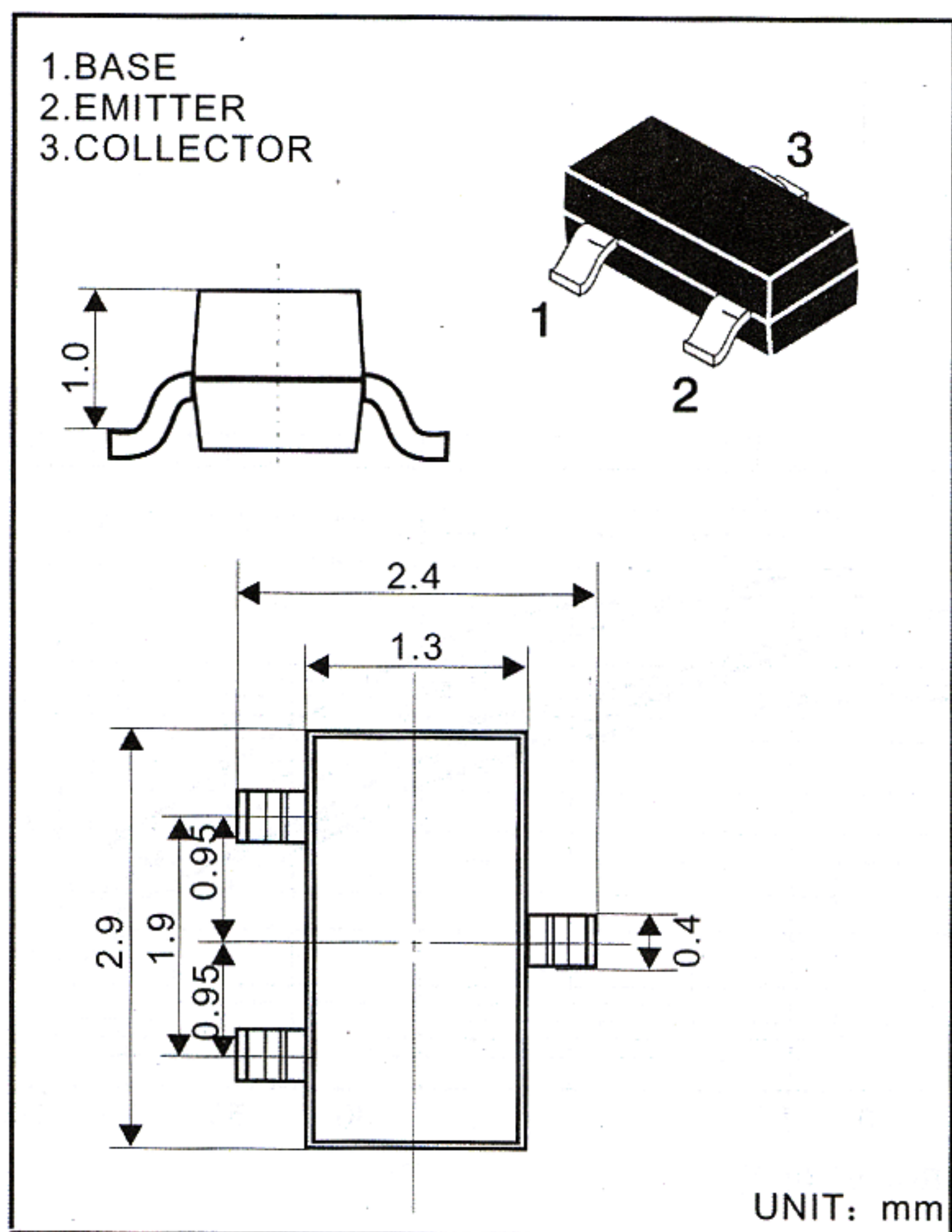


MMBT5551LT1 TRANSISTOR (NPN)



FEATURES

Power dissipation

P_{CM} : 0.3 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : 0.6 A

Collector-base voltage

$V_{(BR)CBO}$: 180V

Operating and storage junction temperature range

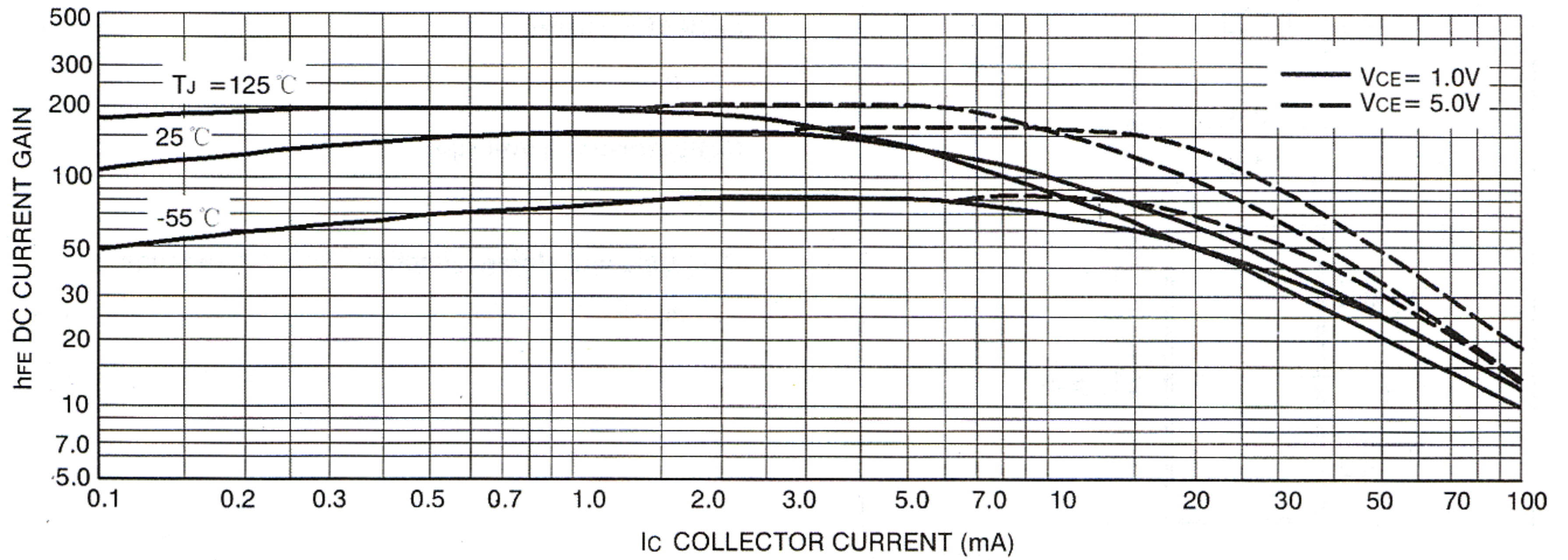
T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

ELECTRICAL CHARACTERISTICS

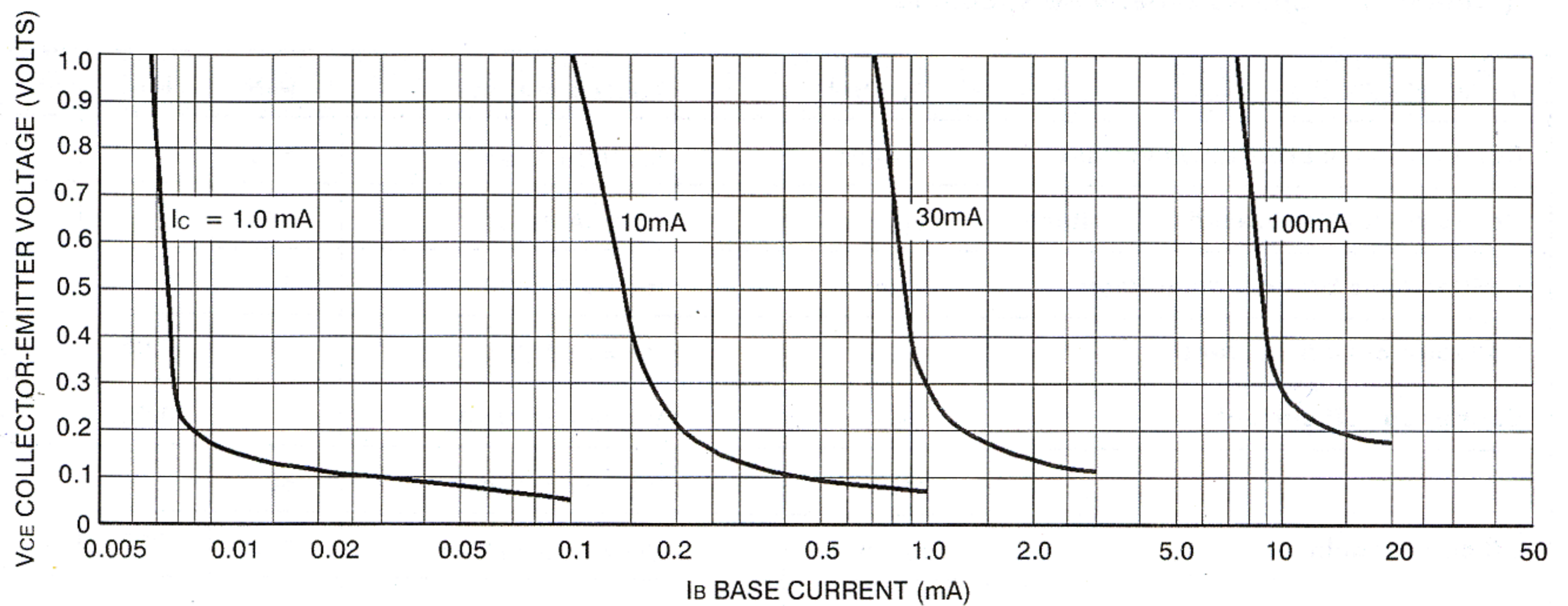
($T_{amp}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	180		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	160		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_B=0$	6		V
Collector cut-off current	I_{CBO}	$V_{CB}=120V, I_E=0$		0.05	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=4V, I_C=0mA$		0.05	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=5V, I_C=1mA$	80		
	$h_{FE(2)}$	$V_{CE}=5V, I_C=10mA$	100	200	
	$h_{FE(3)}$	$V_{CE}=5V, I_C=50mA$	50		
Collector-emitter saturation voltage	V_{CEsat}	$I_C=50mA, I_B=5mA$		0.5	V
Base-emitter saturation voltage	V_{BEsat}	$I_C=50mA, I_B=5mA$		1	V
Transition frequency	f_T	$V_{CE}=5V, I_C=10mA, f=30MHz$	100		MHz

DEVICE MARKING : MMBT5551LT1=G1



DC current Gain



Collector Saturation Region